

Electronic Supplementary Information

In-situ carbon encapsulation of vertical MoS₂ arrays with SnO₂ for durable high rate lithium storage: dominated pseudocapacitive

Mengjiao Li, Qinglin Deng, Junyong Wang, Kai Jiang, Zhigao Hu ^{a)}, and Junhao Chu

Key Laboratory of Polar Materials and Devices (MOE) and Technical Center for Multifunctional Magneto-Optical Spectroscopy (Shanghai), Department of Electronic Engineering, East China Normal University, Shanghai 200241, China

^{a)} Author to whom correspondence should be addressed.

Tel.: +86-21-54345150. Fax: +86-21-54345119.

Electronic mail: zghu@ee.ecnu.edu.cn

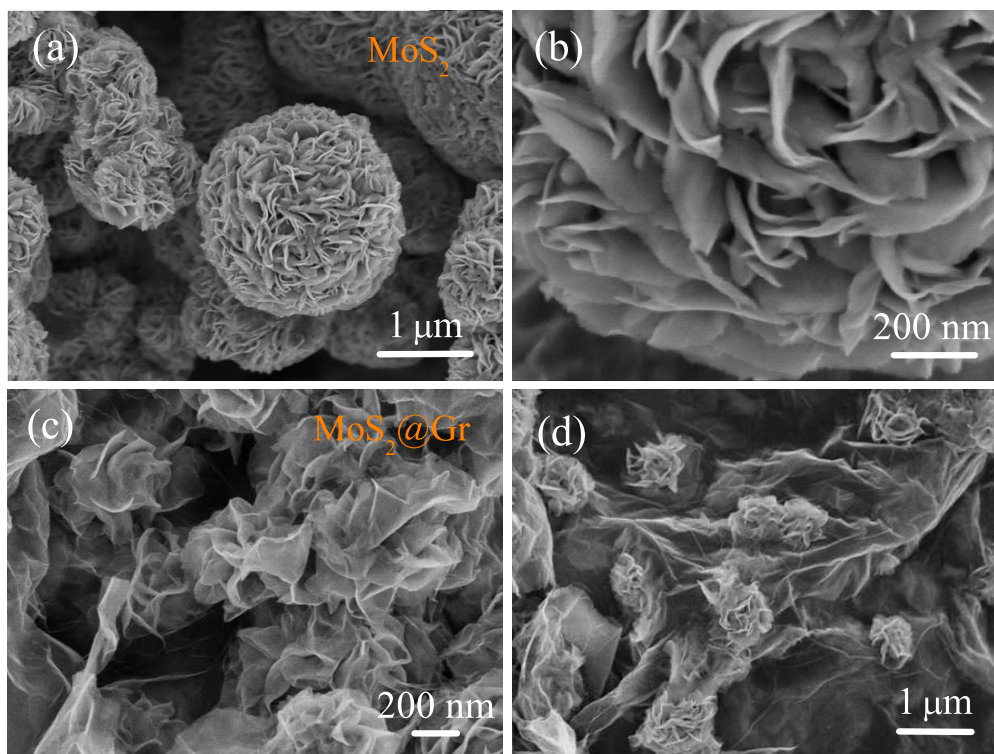


Figure 1: SEM images of (a)-(b) pure MoS₂ and (c)-(d) MoS₂@Gr composites at different magnifications.

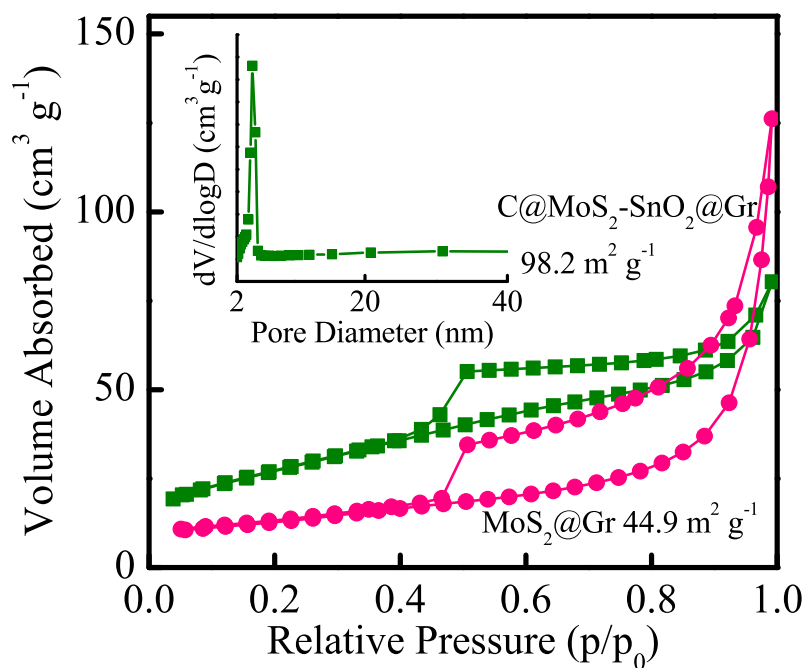


Figure 2: Nitrogen adsorption-desorption isotherms and the pore-size distribution (inset) of C@MoS₂-SnO₂@Gr and MoS₂.

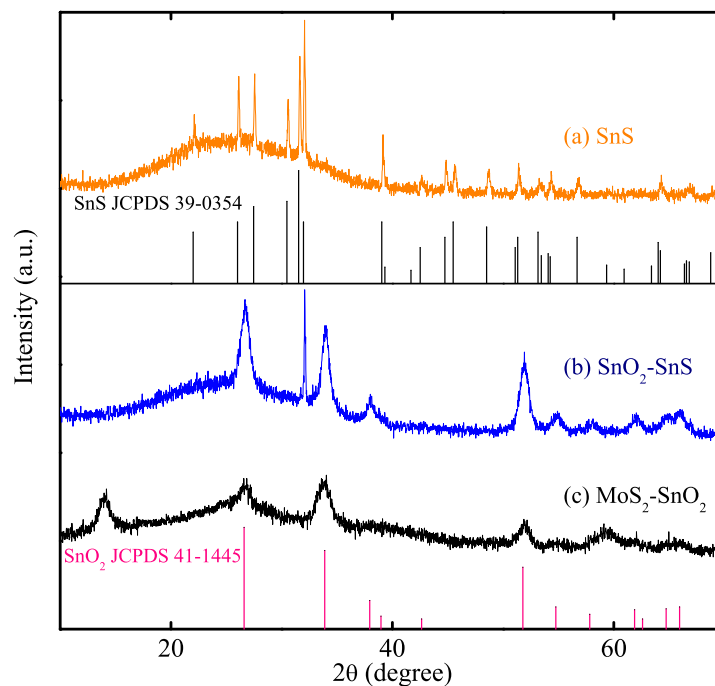


Figure 3: The XRD pattern of (a) SnS (JCPDS 39-0354) obtained from H_2SnO_3 precursor and thioacetamide; (b) SnO_2 -SnS collected from H_2SnO_3 precursor and thiourea; (c) MoS_2 - SnO_2 obtained from $\text{Na}_2\text{MoO}_4 \cdot 2\text{H}_2\text{O}$, H_2SnO_3 precursor, and thiourea.

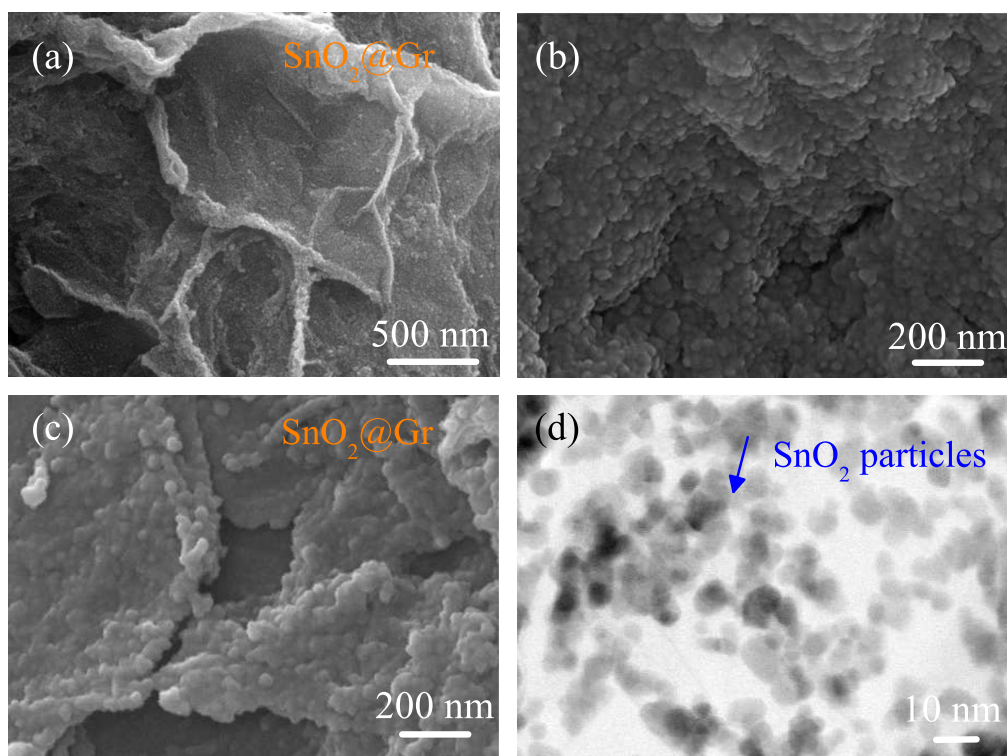


Figure 4: (a)-(c) SEM images and (d) TEM images of SnO_2 @Gr at different magnifications. Note that the size of the SnO_2 nanoparticles reach about 5-8 nm.

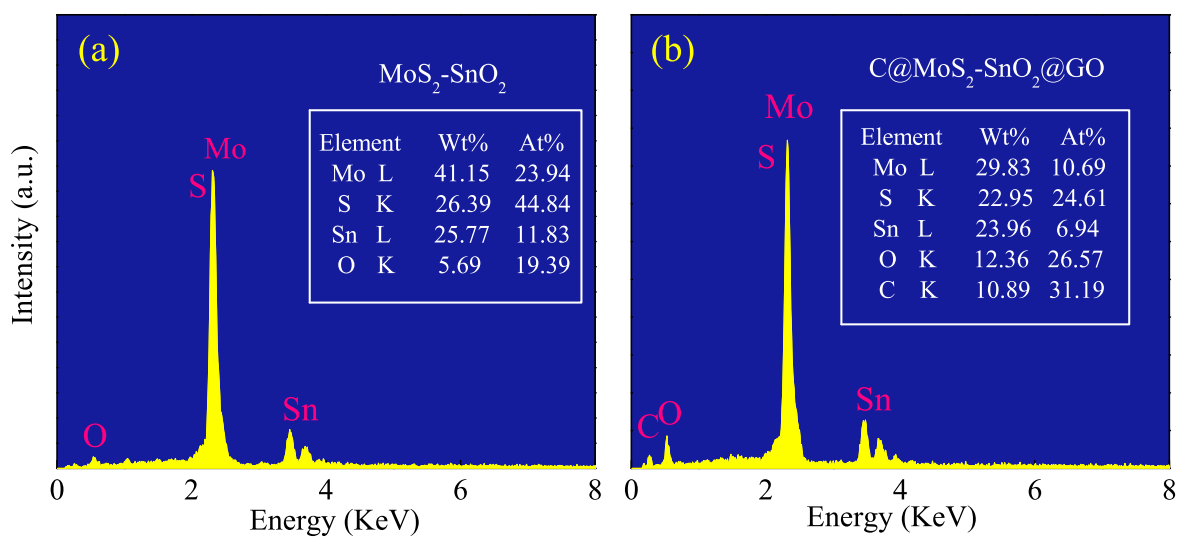


Figure 5: EDS spectra of (a) MoS₂-SnO₂ and (b) C@MoS₂-SnO₂@Gr samples, respectively.

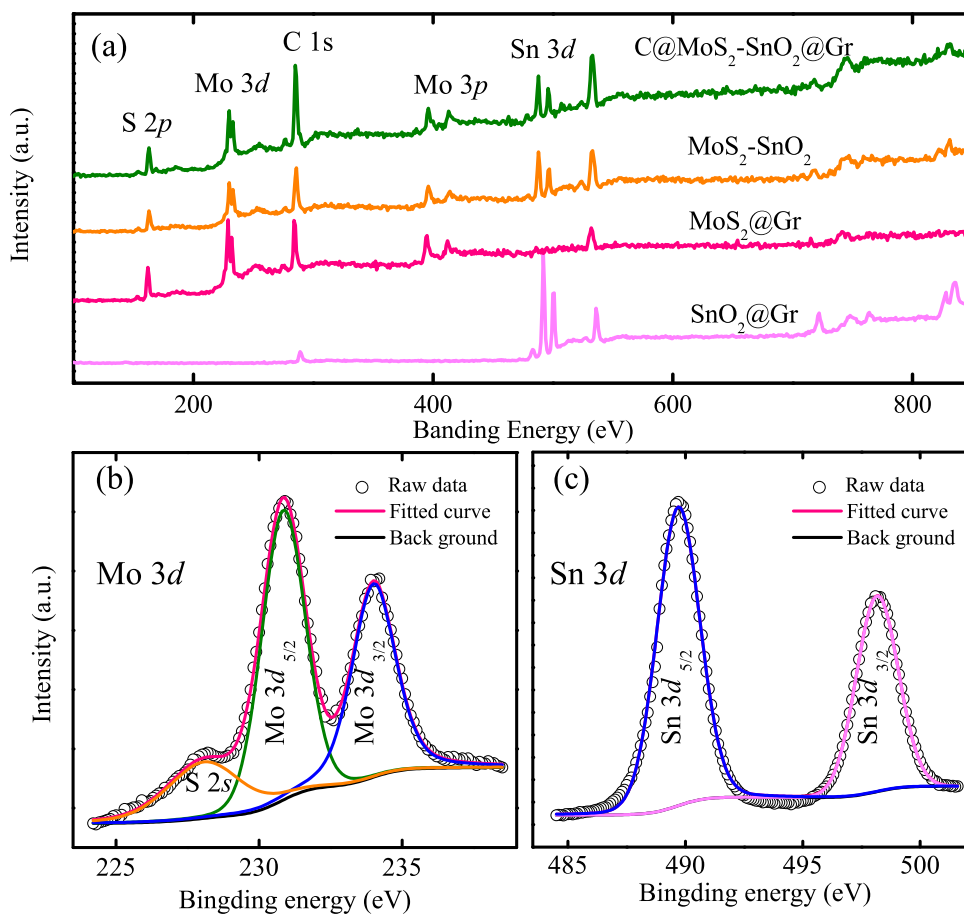


Figure 6: (a) The XPS survey spectra of as-fabricated samples. The high-resolution and fitted resulted of (b) Mo 3d and (c) Sn 3d of MoS₂@Gr and SnO₂@Gr hybrids, respectively.

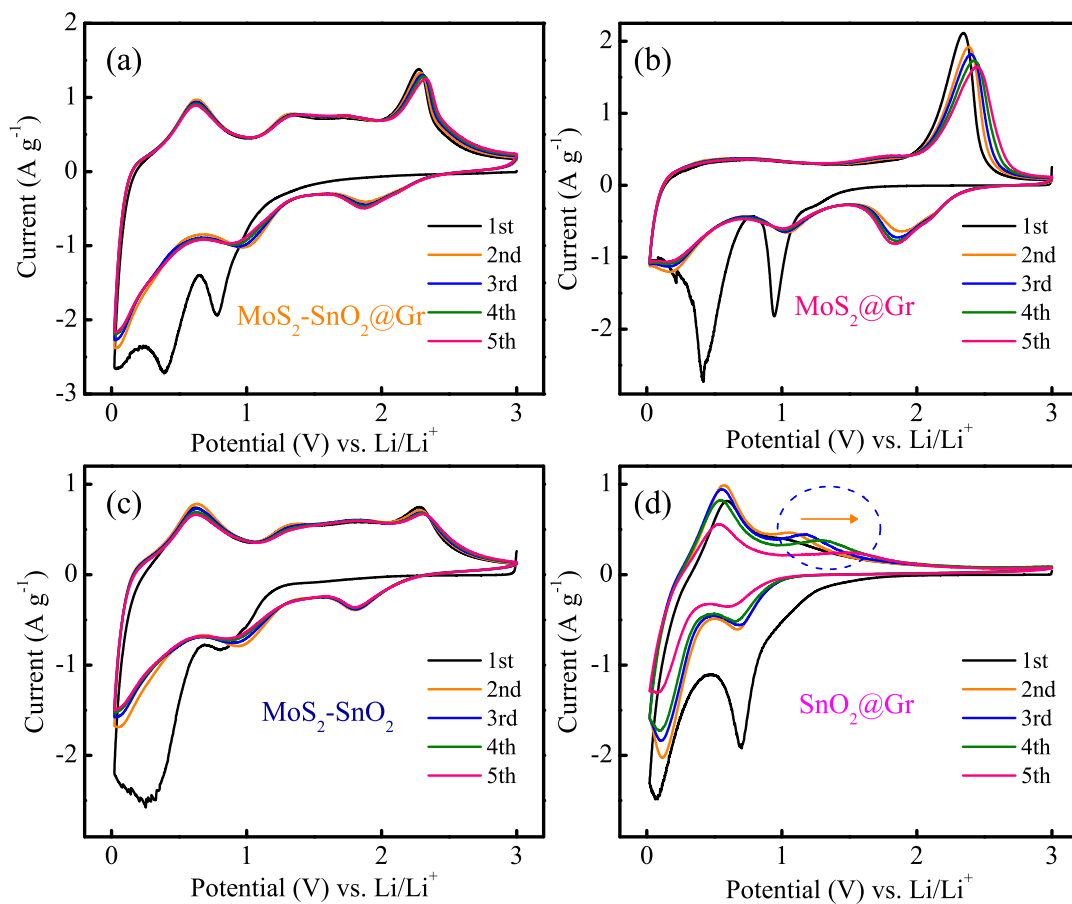


Figure 7: (a)-(d) Cyclic voltammograms (CV) curves for the first five cycles of $\text{MoS}_2\text{-SnO}_2@\text{Gr}$, $\text{MoS}_2@\text{Gr}$, $\text{MoS}_2\text{-SnO}_2$, and $\text{SnO}_2@\text{Gr}$, respectively.

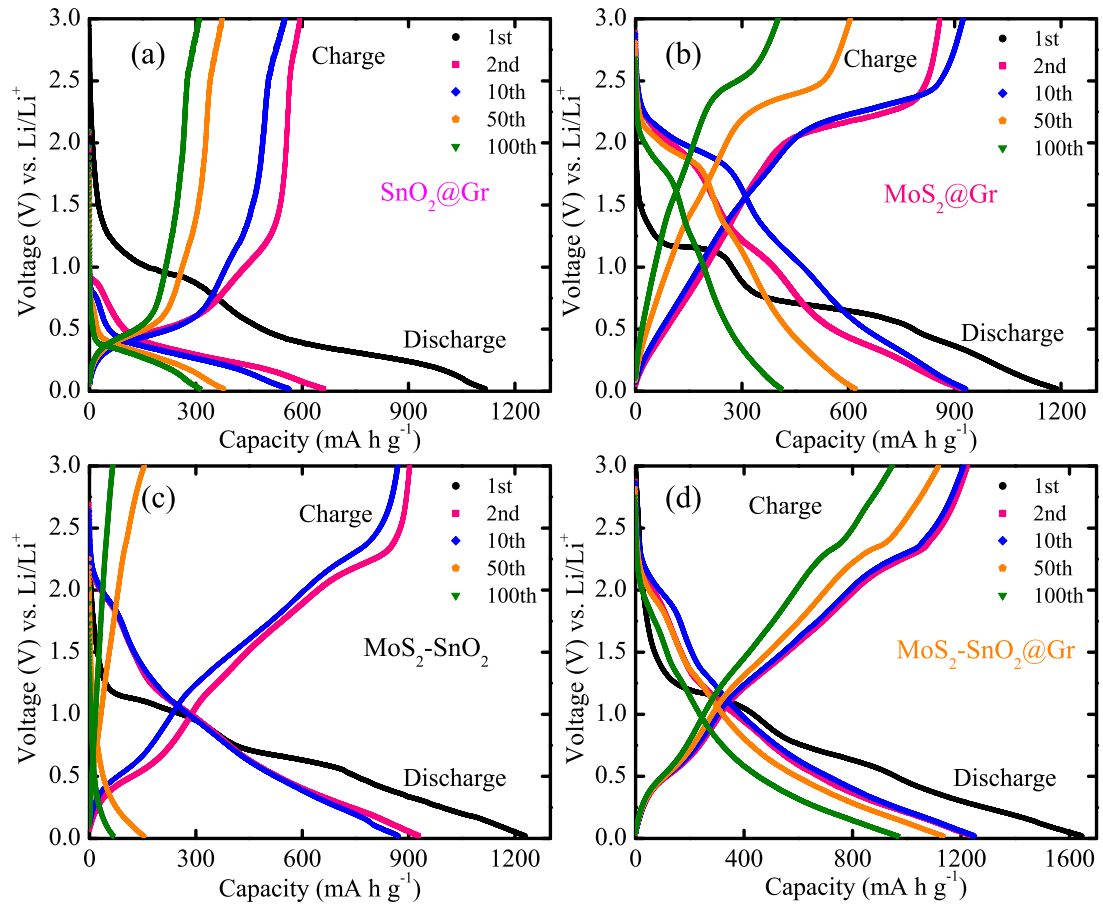


Figure 8: (a)-(d) The galvanostatic discharge-charge (GDC) profiles of $\text{SnO}_2@\text{Gr}$, $\text{MoS}_2@\text{Gr}$, $\text{MoS}_2\text{-SnO}_2$, and $\text{MoS}_2\text{-SnO}_2@\text{Gr}$ for 1st, 2nd, 10th, 50th, and 100th cycles at 0.1 A g^{-1} .

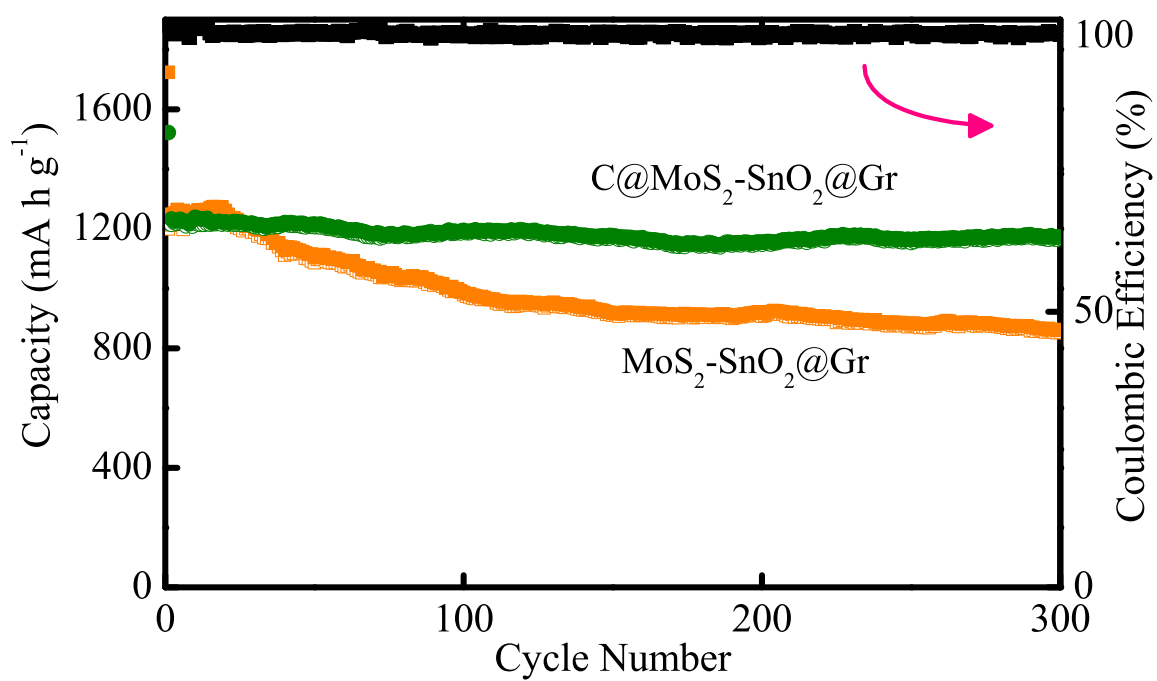


Figure 9: (a)-(d) The cycling stability of the C@MoS₂-SnO₂@Gr and MoS₂-SnO₂@Gr electrodes at 0.1 A g⁻¹ for 300 cycles.

Table 1: Recent works of MoS₂/SnO₂ graphene-based anode materials for LIBs

Anode materials	discharge current density (mA g ⁻¹)	cycle	capacity (mA h g ⁻¹)	capacity retention	Ref.
MoS ₂ @vertical-Gr	200	100th	1109	88%	1
MoS ₂ @Gr	1000	200th	740	84%	2
MoS ₂ @crumpled-Gr	500	250th	680	60%	3
Polypyrrole-SnO ₂	200	200th	790	72%	4
Polyaniline-C-SnO ₂ @Gr	1000	100th	540	70%	5
C-Sn-MoS ₂ -SnO ₂	200	100th	861	80%	6
C@MoS ₂ -SnO ₂ @Gr	100	300th	1170	95%	This work
C@MoS ₂ -SnO ₂ @Gr	800	200th	1070	90%	This work

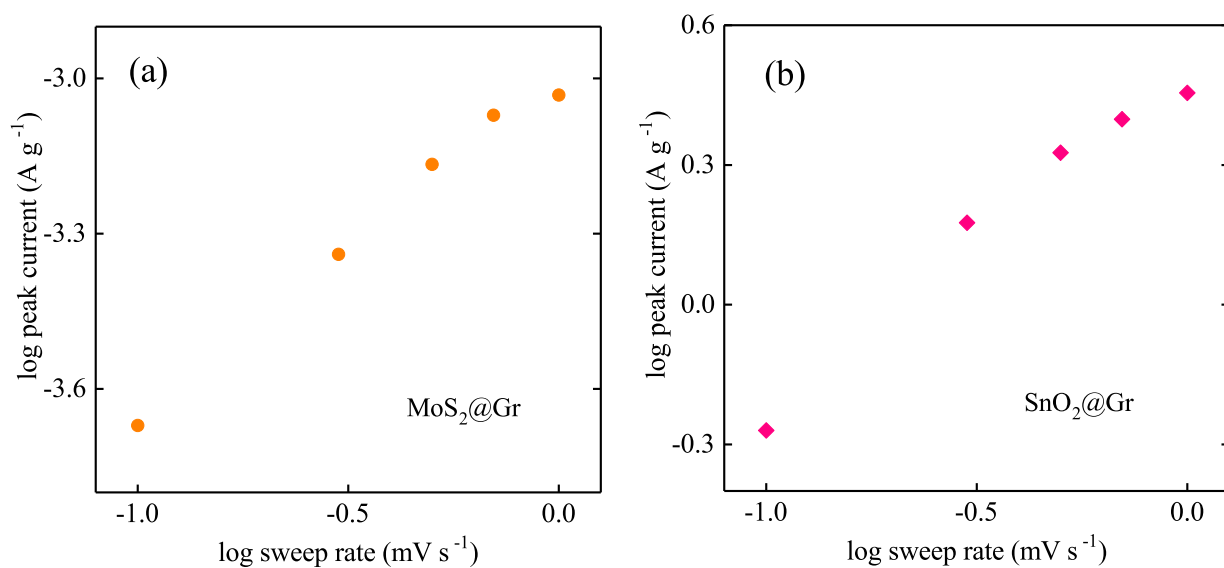


Figure 10: The specific peak currents at various sweep rates from 0.1-1 mV s⁻¹ of (a) MoS₂@Gr and (b) SnO₂@Gr, respectively.

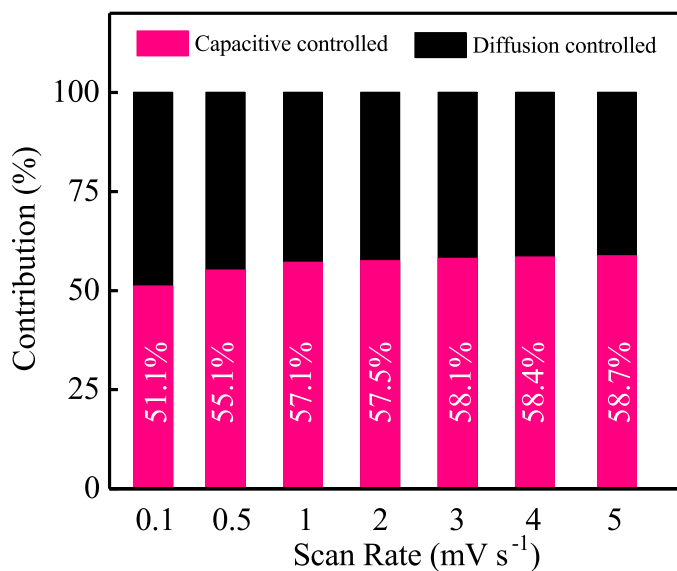


Figure 11: Normalized capacitive contribution ratio of MoS₂@Gr electrode at various rates.

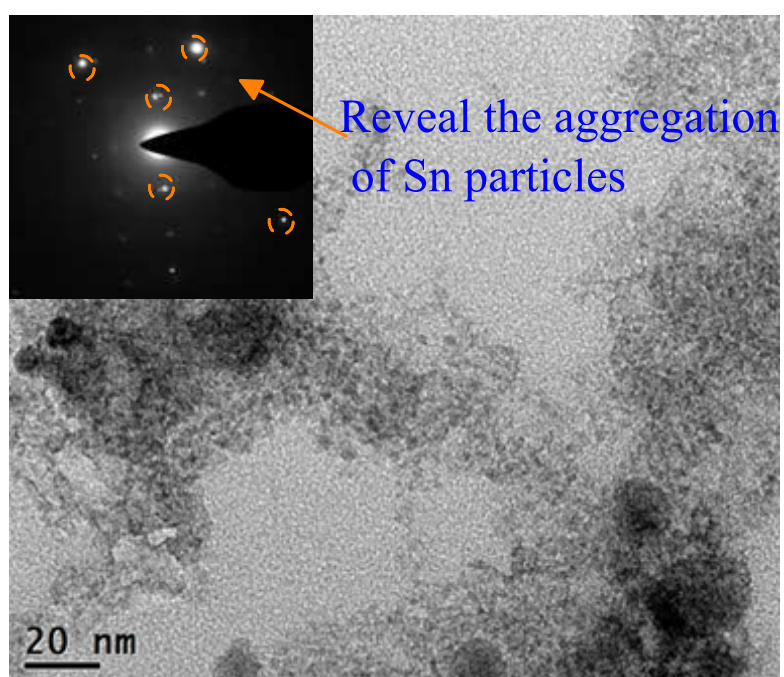


Figure 12: The TEM image of $\text{SnO}_2@\text{Gr}$ electrode after GDC cycles. The inset is the SEAD pattern, which reveals the worse reversibility of SnO_2 and serious aggregation of Sn particles.

References

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